HALOGEN

FREE





P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
	0.165 at V _{GS} = - 4.5 V	- 0.95		
- 12	0.220 at V _{GS} = - 2.5 V	- 0.82		
	0.280 at V _{GS} = - 1.8 V	- 0.67		

SC-89 (6-LEADS) D 1 6 D Marking Code G 3 View Marking Code O WL Lot Traceability and Date Code Part Number Code

Ordering Information: Si1039X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Low Threshold
- Smallest LITTLE FOOT[®] Package:
 1.6 mm x 1.6 mm
- Low 0.6 mm Profile
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Cell Phones and Pagers
 - Load Switch

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 12			
Gate-Source Voltage		V _{GS}	± 8		V	
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	- I _D	- 0.95	- 0.87		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 0.76	- 0.69		
Pulsed Drain Current		I _{DM}	- 4		Α	
Continuous Diode Current (Diode Conduction) ^a		I _S	- 0.18	- 0.14		
Maximum Davier Dissipations	T _A = 25 °C	P _D	0.21	0.17	W	
Maximum Power Dissipation ^a	T _A = 70 °C] ' ['] D	0.13	0.10		
Operating Junction and Storage Temperature Range	ge	T _J , T _{stq}	sta - 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maniana Institut to Ambienta	t ≤ 5 s	- R _{thJA}	500	600	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	□thJA	600	720	C/VV	

Notes:

a. Surface mounted on 1" x 1" FR4 board with minimum copper.

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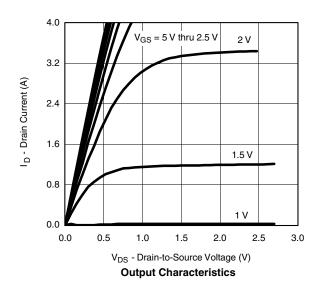
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	ate Threshold Voltage V _{GS(th)}		- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zone Cote Voltone Dunin Comment	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V	-1		- 1		
Zero Gate Voltage Drain Current		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 70 °C			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 4			Α	
		V _{GS} = - 4.5 V, I _D = - 0.87 A		0.140	0.165	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 0.75 A		0.180	0.220		
		V _{GS} = - 1.8 V, I _D = - 0.2 A		0.230	0.280	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 0.87 A		3.5		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 0.14 A, V _{GS} = 0 V		- 0.78	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			3.8	6		
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.87 \text{ A}$		0.7		nC	
Gate-Drain Charge	Q_{gd}			0.8			
Turn-On Delay Time	t _{d(on)}			15	30		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 12 Ω		20	40		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong\text{-}\ 0.5\ \text{A},\ \text{V}_\text{GEN}=\text{-}\ 4.5\ \text{V},\ \text{R}_g=6\ \Omega$		30	60	ns	
Fall Time	t _f			16	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 0.14 A, dI/dt = 100 A/μs		20	40		

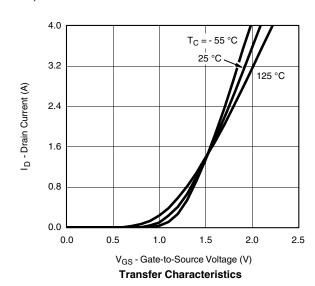
Notes:

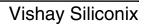
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





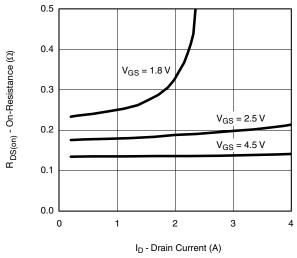




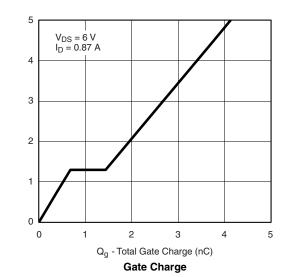
V_{GS} - Gate-to-Source Voltage (V)

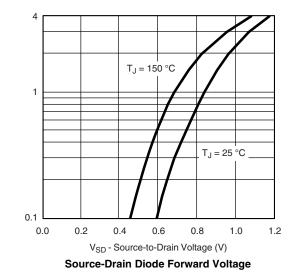
Is - Source Current (A)

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



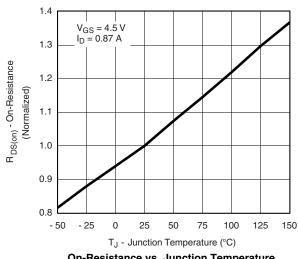
On-Resistance vs. Drain Current



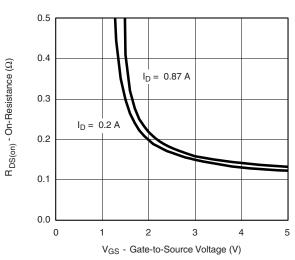


800 600 C - Capacitance (pF) 400 Coss 200 0 2 10 12 0 6

V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature

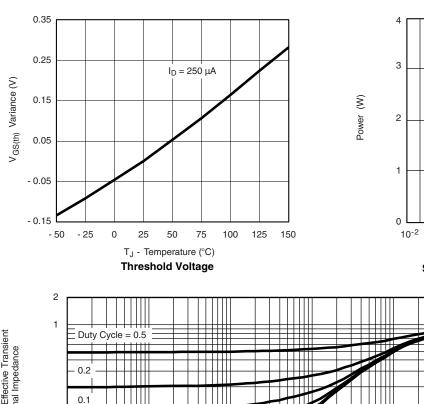


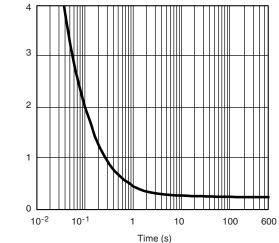
On-Resistance vs. Gate-to-Source Voltage

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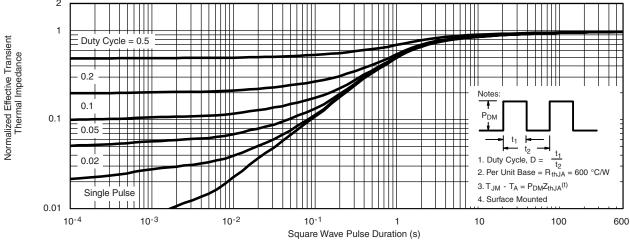
VISHAY.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Power, Junction-to-Ambient

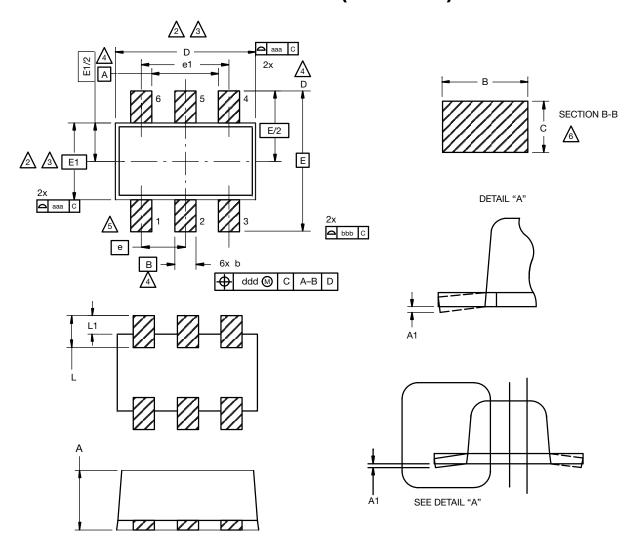


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?70682.



SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

ADatums A, B and D to be determined 0.10 mm from the lead tip.

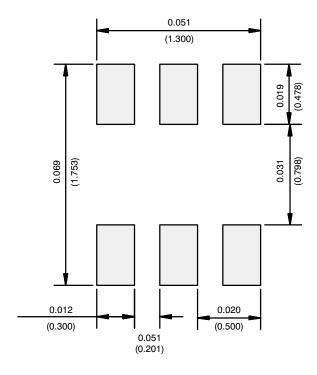
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS					
	MIN.	NOM.	MAX.			
Α	0.56	0.58	0.60			
A1	0	0.02	0.10			
b	0.15	0.22	0.30			
С	0.10	0.14	0.18			
D	1.50	1.60	1.70			
E	1.50	1.60	1.70			
E1	1.15	1.20	1.25			
е	0.45	0.50	0.55			
e1	0.95	1.00	1.05			
L	0.25	0.35	0.50			
L1	0.10	0.20	0.30			
C14-0439-Rev. C, 11-Aug-14 DWG: 5880						



RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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